



# PJW4P06A

## 60V P-Channel Enhancement Mode MOSFET

Voltage      -60 V      Current      -4.0 A

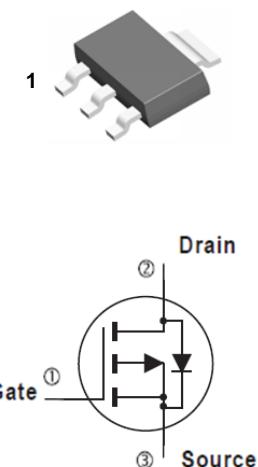
### Features

- $R_{DS(ON)}$ ,  $V_{GS} @ -10V, I_D @ -4.0A < 110m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS} @ -4.5V, I_D @ -2.0 A < 130m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123 grams
- Marking: W4P06A

SOT-223



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current  $T_A=25^\circ C$	$I_D$	-4	A
$T_A=70^\circ C$	$I_D$	-3.2	
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	-16	A
Power Dissipation  $T_A=25^\circ C$	$P_D$	3.1	W
$T_A=70^\circ C$	$P_D$	2	
Single Pulse Avalanche Energy <sup>(Note 5)</sup>	$E_{AS}$	12.8	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150	°C
Typical Thermal resistance - Junction to Ambient <sup>(Note 6)</sup>	$R_{\theta JA}$	40.3	°C/W

- Limited only By Maximum Junction Temperature



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## Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.7	-2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4.0A$	-	87	110	$m\Omega$
		$V_{GS}=-4.5V, I_D=-2.0A$	-	110	130	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-60V, V_{GS}=0V$	-	-	-1.0	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>Dynamic</b> (Note 7)						
Total Gate Charge	$Q_g$	$V_{DS}=-30V, I_D=-4.0A,$ $V_{GS}=-10V$ (Note 1,2)	-	10	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.6	-	
Gate-Drain Charge	$Q_{gd}$		-	3	-	
Input Capacitance	$C_{iss}$	$V_{DS}=-30V, V_{GS}=0V,$ $f=1.0MHz$	-	785	-	pF
Output Capacitance	$C_{oss}$		-	175	-	
Reverse Transfer Capacitance	$C_{rss}$		-	112	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-30V, RL=30\Omega$ $V_{GS}=-10V, R_G=6.2\Omega$ (Note 1,2)	-	8	-	ns
Turn-On Rise Time	$t_r$		-	15	-	
Turn-Off Delay Time	$t_{d(off)}$		-	43	-	
Turn-Off Fall Time	$t_f$		-	8.4	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_S$	---	-	-	-4	A
Diode Forward Voltage	$V_{SD}$	$I_S=-1A, V_{GS}=0V$	-	-0.76	-1.0	V

### NOTES :

1. Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is package limited.
4. Repetitive rating, pulse width limited by junction temperature  $T_J(MAX)=150^\circ C$ . Ratings are based on low frequency and duty cycles to keep initial  $T_J = 25^\circ C$ .
5. The test condition is  $L=0.1mH, I_{AS}=-16A, V_{DD}=-25V, V_{GS}=-10V$
6.  $R_{eJA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
7. Guaranteed by design, not subject to production testing.



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## TYPICAL CHARACTERISTIC CURVES

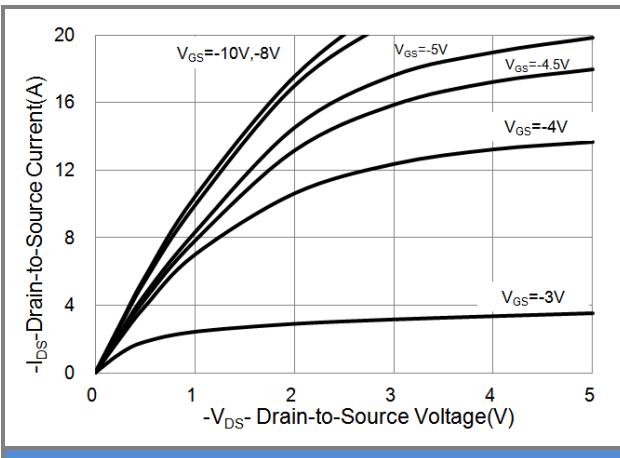


Fig.1 Output Characteristics

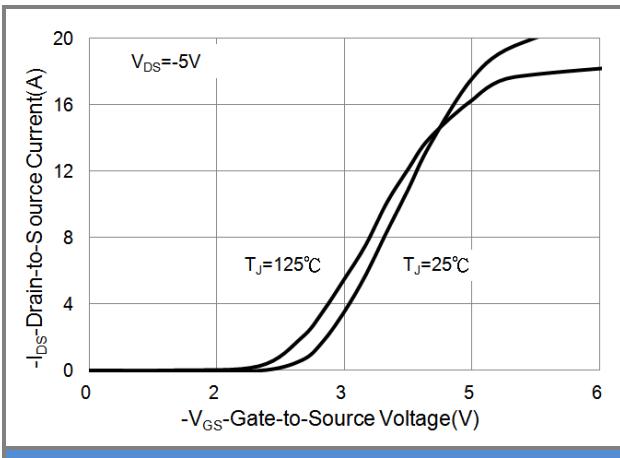


Fig.2 Transfer Characteristics

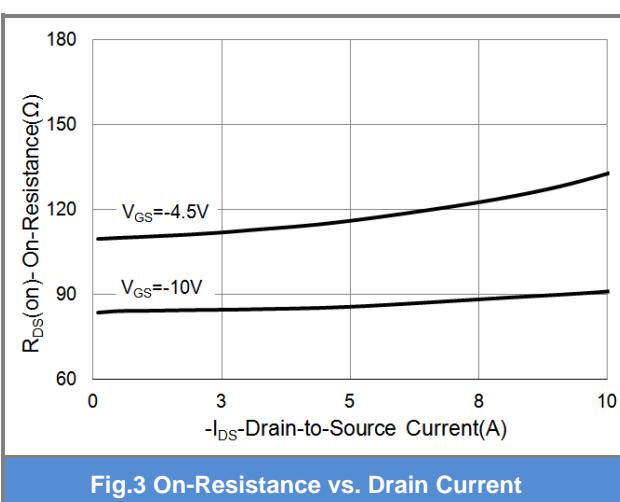


Fig.3 On-Resistance vs. Drain Current

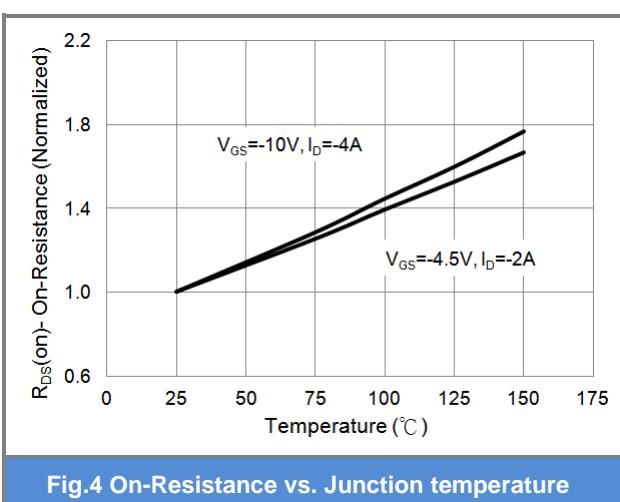


Fig.4 On-Resistance vs. Junction temperature

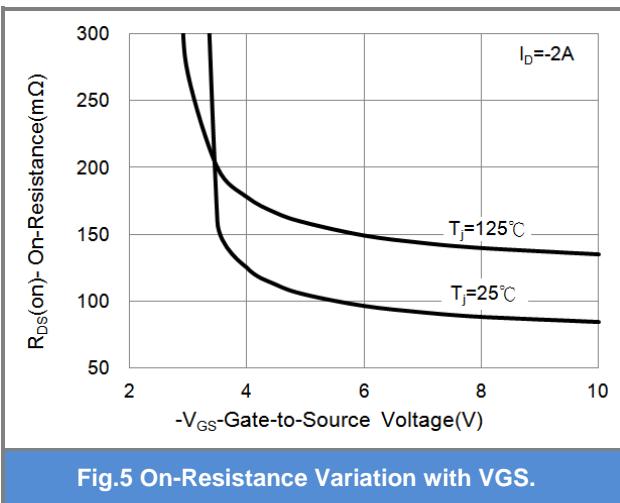


Fig.5 On-Resistance Variation with VGS.

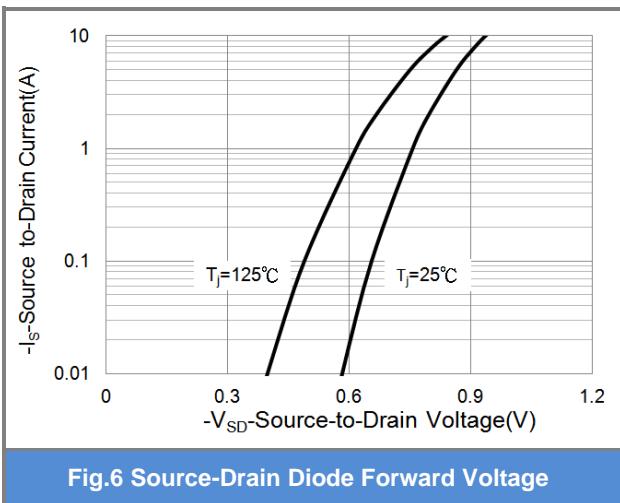


Fig.6 Source-Drain Diode Forward Voltage



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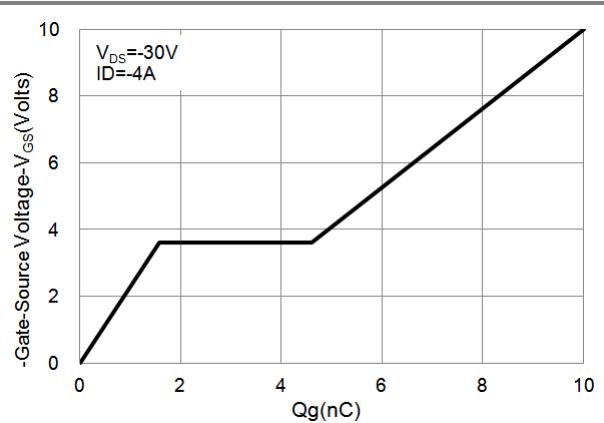


Fig.7 Gate-Charge Characteristics

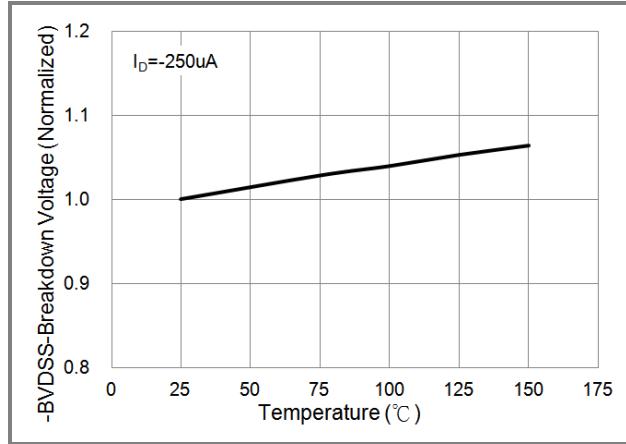


Fig.8 Breakdown Voltage Variation vs. Temperature

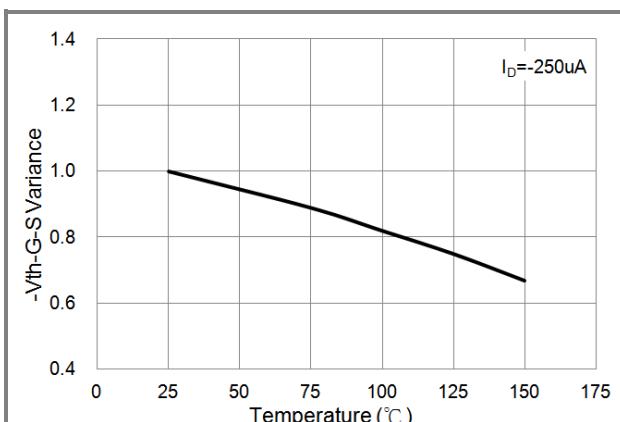


Fig.9 Threshold Voltage Variation with Temperature

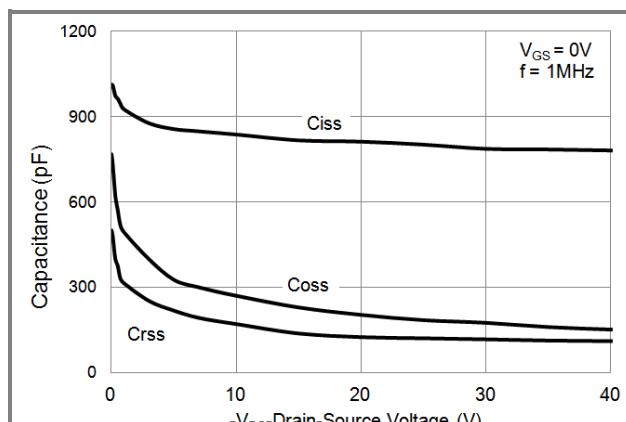


Fig.10 Capacitance vs. Drain-Source Voltage

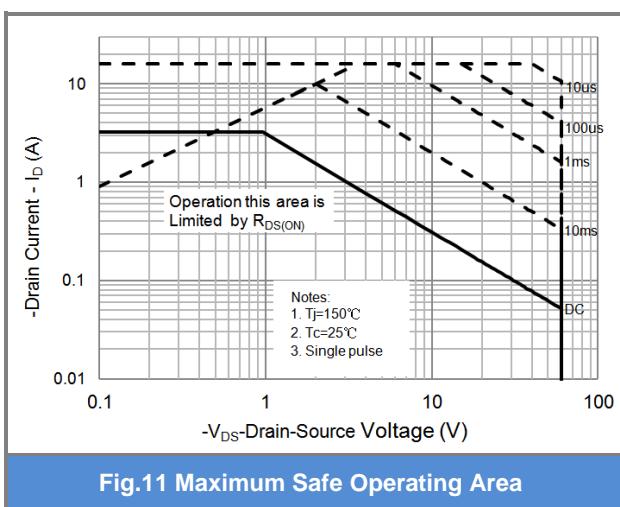


Fig.11 Maximum Safe Operating Area



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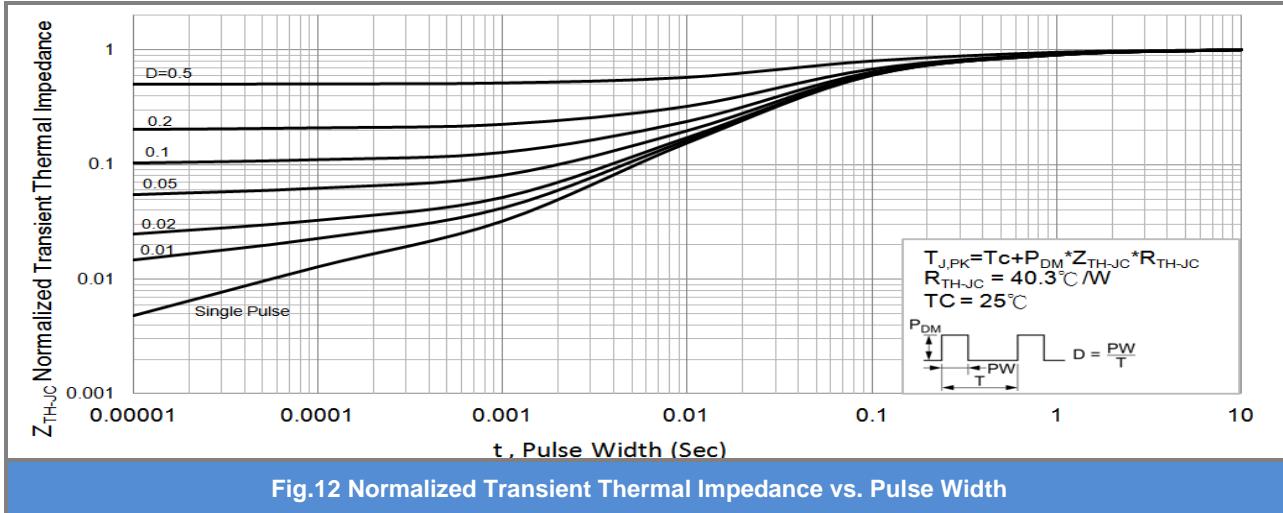
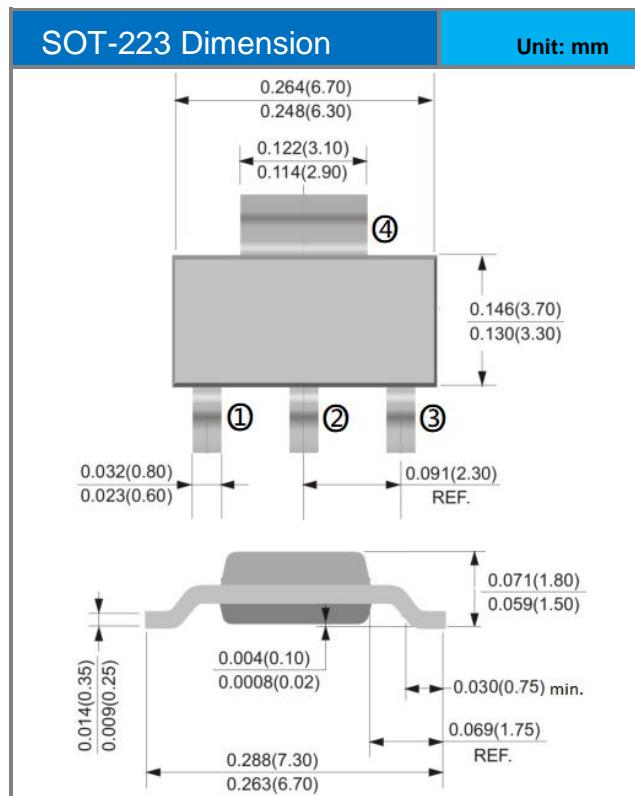


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width



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## Packaging Information





# PJW4P06A

## PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJW4P06A_R2_00001	SOT-223	2,500pcs / 13" reel	W4P06A	Halogen free

## MOUNTING PAD LAYOUT

